

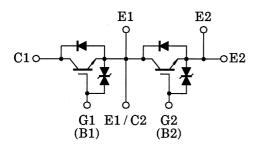
TOSHIBA GTR Module Silicon N Channel IGBT

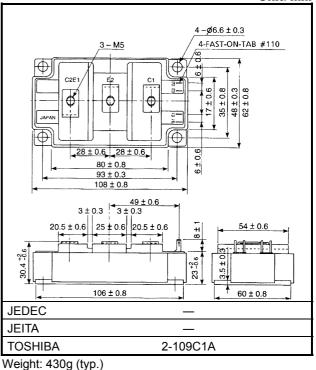
# MG150Q2YS40

High Power Switching applications Motor Control Applications

- High input impedance
- High speed :  $t_f = 0.5 \mu s \text{ (max)}$  $t_{rr} = 0.5 \mu s \text{ (max)}$
- Low saturation voltage
  - : VCE (sat) = 4.0V (max)
- Enhancement-mode
- Includes a complate half bridge in one package.
- The electrodes are isolated from case.

#### **Equivalent Circuit**





#### Maximum Ratings (Ta = 25°C)

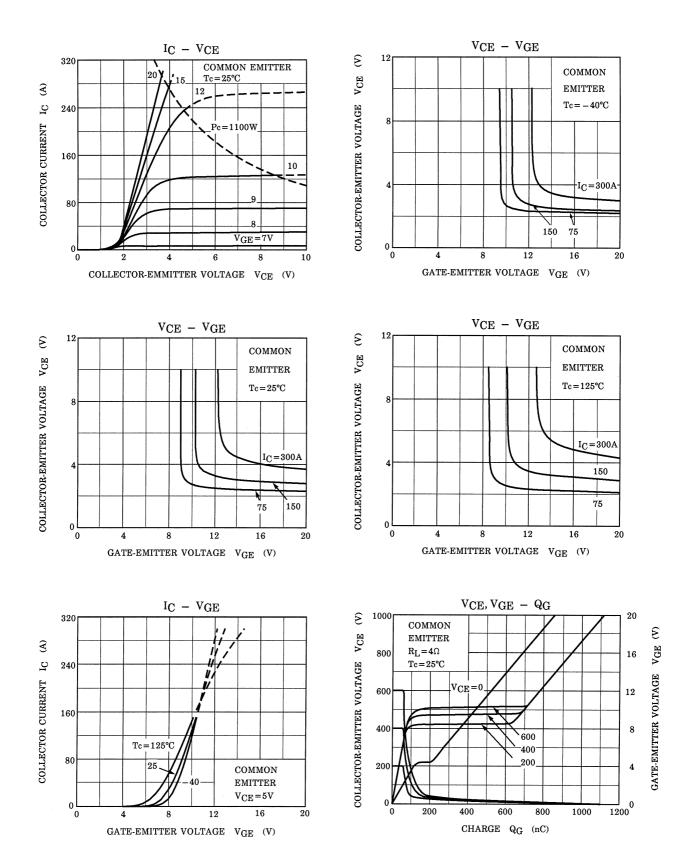
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	1200	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	Ι <sub>C</sub>	150	A	
	1ms	I <sub>CP</sub>	300		
Forward current	DC	١ <sub>F</sub>	150	A	
	1ms	I <sub>FM</sub>	300		
Collector power dissipation (Tc = 25°C)		PC	1100	W	
Junction temperature		Тј	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−</b> 40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N∙m	

Unit: mm

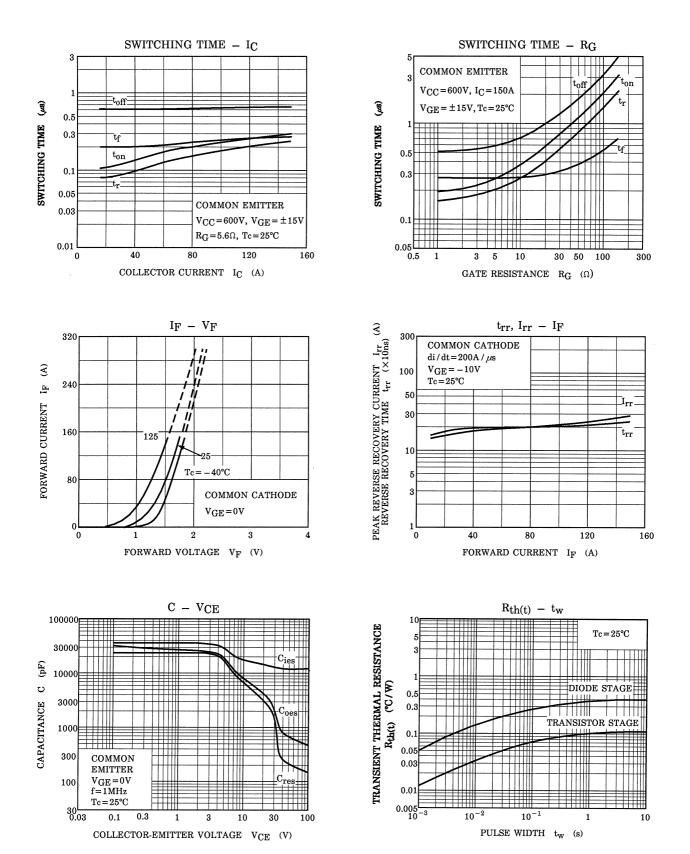
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GES</sub>	$V_{GE}$ = ±20V, $V_{CE}$ = 0	_	_	±20	μA	
Collector cut-off current		ICES	V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0	_	_	2.0	mA	
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 150mA , V <sub>CE</sub> = 5V	3.0	_	6.0	V	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 150A, V <sub>GE</sub> = 15V	_	3.0	4.0	V	
Input capacitance		C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	_	18000	_	pF	
Switching time	Rise time	t <sub>r</sub>	$15V_{0} \xrightarrow{5.6\Omega}_{-15V} \xrightarrow{600V}_{-00V}$	_	0.3	0.6	μs	
	Turn-on time	t <sub>on</sub>		_	0.4	0.8		
	Fall time	t <sub>f</sub>			0.2	0.5		
	Turn-off time	t <sub>off</sub>			0.8	1.5		
Forward voltage		VF	I <sub>F</sub> = 150A, V <sub>GE</sub> = 0		2.0	3.0	V	
Reverse recovery time		t <sub>rr</sub>	I <sub>F</sub> = 150A, V <sub>GE</sub> = −10V di / dt = 200A / μs	_	0.25	0.5	μs	
Thermal resistance		R <sub>th (j-c)</sub>	Transistor	_	_	0.11	0.11 °C/W	
			Diode	_	_	0.4		

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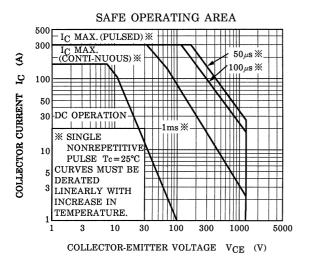


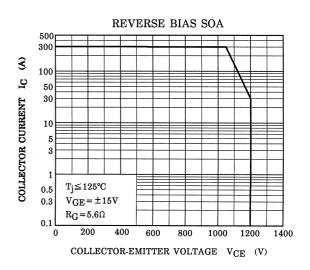
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2001-08-16

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